

**Enhancing T_c in field-doped Fullerenes by
applying uniaxial stress**

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Capitalizing on the two-dimensional nature of superconductivity in field-effect doped C_{60} , we show that it should be possible to increase the transition temperature T_c by applying uniaxial stress perpendicular to the gate electrode. This method not only holds the promise of substantially enhancing T_c (by about 30 K per GPa), but also provides a sensitive check of the current understanding of superconductivity in the doped Fullerenes.